TOSHIBA Transistor Silicon NPN Epitaxial Planar Type

2SC5110

For VCO Application

Unit: mm

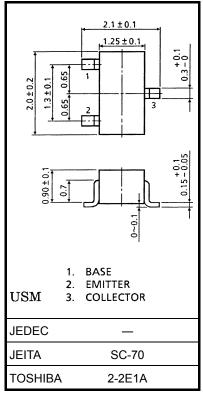
Absolute Maximum Ratings (Ta = 25°C)

Characteristics	Symbol	Rating	Unit	
Collector-base voltage	V_{CBO}	20	V	
Collector-emitter voltage	V _{CEO}	10	V	
Emitter-base voltage	V _{EBO}	3	V	
Base current	ΙΒ	30	mA	
Collector current	IC	60	mA	
Collector power dissipation	PC	100	mW	
Junction temperature	Tj	125	°C	
Storage temperature range	T _{stg}	-55~125	°C	

Note:

Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/"Derating Concept and Methods") and individual reliability data (i.e. reliability test report and estimated failure rate, etc).



Weight: 0.006 g (typ.)

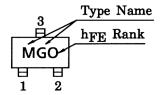
Electrical Characteristics (Ta = 25°C)

Characteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Collector cut-off current	I _{CBO}	$V_{CB} = 10 \text{ V}, I_{E} = 0$	_	_	0.1	μА
Emitter cut-off current	I _{EBO}	V _{EB} = 1 V, I _C = 0	_	_	0.1	μА
DC current gain	h _{FE} (Note 1)	V _{CE} = 5 V, I _C = 5 mA	80	_	240	
Transition frequency	f _T	V _{CE} = 5 V, I _C = 5 mA	3	5	_	GHz
Insertion gain	S _{21e} ²	$V_{CE} = 5 \text{ V}, I_{C} = 5 \text{ mA}, f = 1 \text{ GHz}$	6	10	_	dB
Output capacitance	C _{ob}	V _{CB} = 5 V, I _E = 0, f = 1 MHz (Note 2)	_	0.9	_	pF
Reverse transfer capacitance	C _{re}	VCB = 0 V, $IE = 0$, $I = 1$ IVITZ (NOTE 2)	_	0.7	1.1	pF
Collector-base time constant	C _c .rbb'	$V_{CB} = 5 \text{ V}, I_{C} = 3 \text{ mA}, f = 30 \text{ MHz}$		6	11	ps

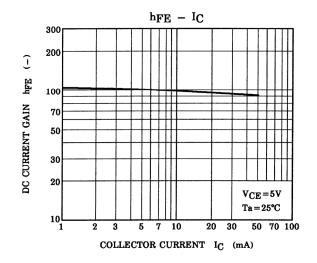
Note 1: hFE classification O: 80~160, Y: 120~240

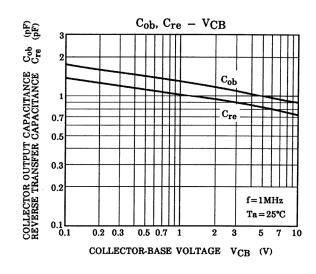
Note 2: C_{re} is measured by 3 terminal method with capacitance bridge.

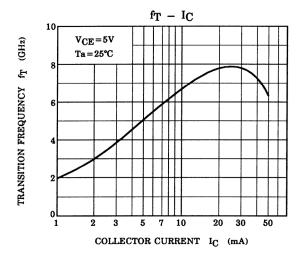
Marking

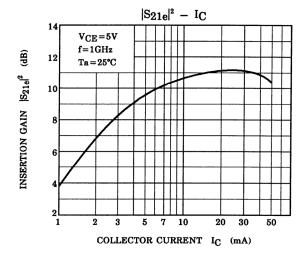


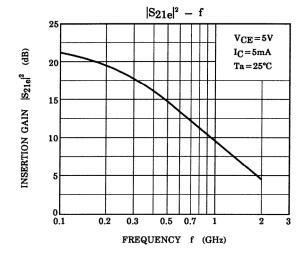
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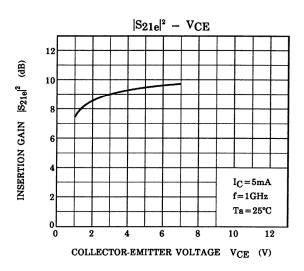




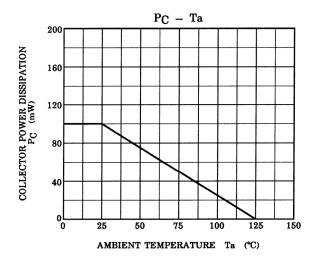








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S-Parameter $Z_O = 50 \Omega$, $Ta = 25^{\circ}C$

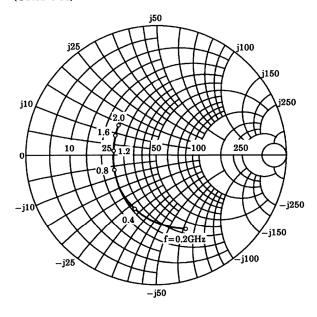
$V_{CE} = 5 V$, $I_C = 5 mA$

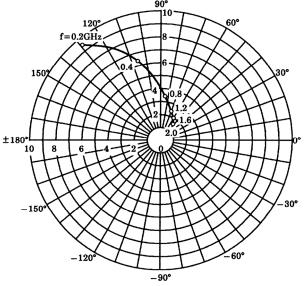
Frequency	S	11	S	21	S1	12	S	22
(MHz)	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.	Mag.	Ang.
200	0.631	-67.7	9.526	129.8	0.062	55.9	0.687	-38.7
400	0.441	-111.7	6.393	106.3	0.084	49.5	0.459	-48.5
600	0.363	-139.8	4.611	93.6	0.100	50.6	0.360	-50.6
800	0.338	-159.8	3.599	84.6	0.117	52.9	0.312	-51.1
1000	0.331	-175.0	2.990	77.5	0.134	55.1	0.286	-51.6
1200	0.337	171.9	2.556	71.2	0.152	57.2	0.271	-53.0
1400	0.344	161.7	2.252	65.3	0.174	58.6	0.265	-55.7
1600	0.359	152.1	2.011	60.3	0.196	58.5	0.259	-59.5
1800	0.373	144.6	1.845	55.4	0.217	57.9	0.254	-63.6
2000	0.391	138.5	1.691	50.8	0.238	58.3	0.249	-68.8

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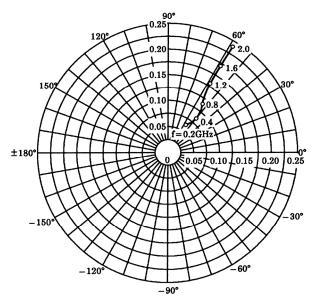
 $\begin{array}{l} S_{11e} \\ V_{CE} = 5V \\ I_{C} = 5mA \\ T_{a} = 25^{\circ}C \\ (UNIT:\Omega) \end{array}$

 $\begin{array}{c} S_{21e} \\ V_{CE} = 5V \\ I_{C} = 5mA \\ Ta = 25^{\circ}C \end{array}$



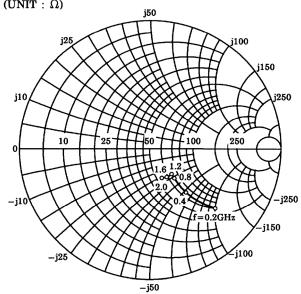


 $\begin{array}{c} S_{12e} \\ V_{CE} = 5V \\ I_{C} = 5mA \\ Ta = 25^{\circ}C \end{array}$



S22e VCE=5V IC=5mA Ta=25°C (UNIT: Ω)

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20070701-EN GENERAL

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